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Team Nexperia

Product data sheet

1. **General description**

The 74LV86 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC86 and 74HCT86.

The 74LV86 provides a quad 2-input exclusive-OR function.

2. **Features**

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical output ground bounce < 0.8 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at V_{CC} = 3.3 V and $T_{amb} = 25 \ ^{\circ}C$
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

Ordering information 3.

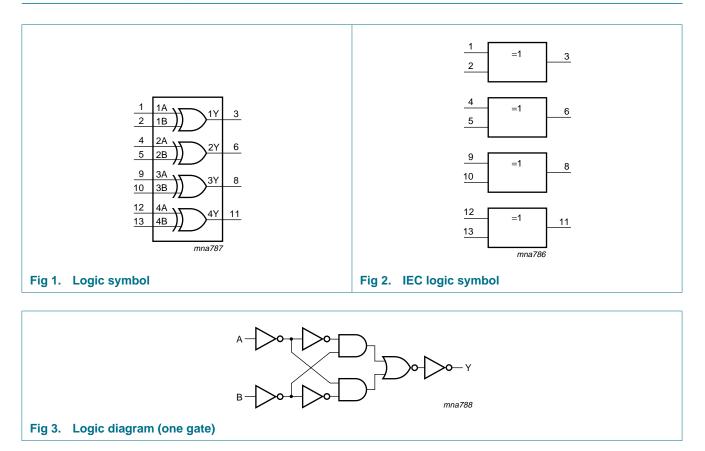
Type number	Package							
	Temperature range	Name	Description	Version				
74LV86N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1				
74LV86D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1				
74LV86DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1				
74LV86PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1				
74LV86BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1				



74LV86

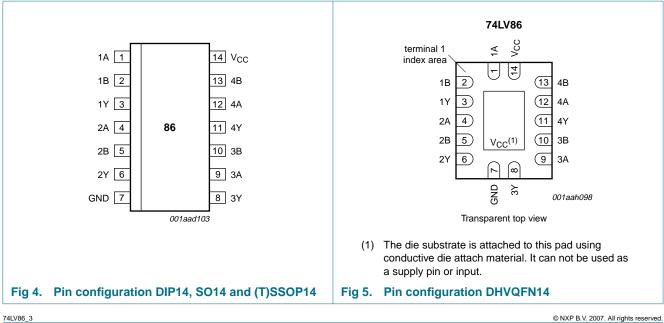
Quad 2-input exclusive-OR gate

4. Functional diagram



5. Pinning information

5.1 Pinning



Product data sheet

Table 2.	Pin description	
Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
ЗA	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
V _{CC}	14	supply voltage

5.2 Pin description

6. Functional description

Table 3.Function table

H = HIGH voltage level; L = LOW voltage level

Input	Output	
nA	nB	nY
L	L	L
L	Н	н
Н	L	н
Н	Н	L

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5$ V or $V_{I} > V_{CC} + 0.5$ V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±50	mA
lo	output current	$V_{O} = -0.5 \text{ V}$ to ($V_{CC} + 0.5 \text{ V}$)	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$			
	DIP14 package		[2] _	750	mW
	SO14 package		<u>[3]</u>	500	mW
	(T)SSOP14 package		<u>[4]</u> _	500	mW
	DHVQFN14 package		<u>[5]</u> _	500	mW

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 12 mW/K above 70 °C.

[3] P_{tot} derates linearly with 8 mW/K above 70 °C.

[4] Ptot derates linearly with 5.5 mW/K above 60 °C.

[5] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage[1]		1.0	3.3	5.5	V
VI	input voltage		0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	V_{CC} = 1.0 V to 2.0 V	-	-	500	ns/V
		V_{CC} = 2.0 V to 2.7 V	-	-	200	ns/V
		V_{CC} = 2.7 V to 3.6 V	-	-	100	ns/V
		V_{CC} = 3.6 V to 5.5 V	-	-	50	ns/V

[1] The static characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V, but LV devices are guaranteed to function down to V_{CC} = 1.0 V (with input levels GND or V_{CC}).

9. Static characteristics

Table 6.Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	–40 °C to	• +125 °C	Unit	
			Min	Typ <mark>[1]</mark>	Max	Min	Max	1	
VIH	HIGH-level input voltage	V _{CC} = 1.2 V	0.9	-	-	0.9	-	V	
		$V_{CC} = 2.0 V$	1.4	-	-	1.4	-	V	
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V	
		V_{CC} = 4.5 V to 5.5 V	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V	
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	0.3	-	0.3	V	
		$V_{CC} = 2.0 V$	-	-	0.6	-	0.6	V	
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V	
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V	
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$							
		$I_{O} = -100 \ \mu\text{A}; \ V_{CC} = 1.2 \ \text{V}$	-	1.2	-	-	-	V	
		$I_{O} = -100 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.8	2.0	-	1.8	-	V	
		I_{O} = $-100~\mu\text{A};~V_{CC}$ = 2.7 V	2.5	2.7	-	2.5	-	V	
		I_O = $-100~\mu\text{A};~V_{CC}$ = 3.0 V	2.8	3.0	-	2.8	-	V	
		I_O = $-100~\mu\text{A};~V_{CC}$ = 4.5 V	4.3	4.5	-	4.3	-	V	
		$I_O = -6$ mA; $V_{CC} = 3.0$ V	2.4	2.82	-	2.2	-	V	
		I_O = -12 mA; V_{CC} = 4.5 V	3.6	4.2	-	3.5	-	V	
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$							
		I_O = 100 $\mu A; V_{CC}$ = 1.2 V	-	0	-	-	-	V	
		I_O = 100 $\mu A; V_{CC}$ = 2.0 V	-	0	0.2	-	0.2	V	
		I_{O} = 100 $\mu A;$ V_{CC} = 2.7 V	-	0	0.2	-	0.2	V	
		I_O = 100 $\mu A; V_{CC}$ = 3.0 V	-	0	0.2	-	0.2	V	
		I_O = 100 $\mu A; V_{CC}$ = 4.5 V	-	0	0.2	-	0.2	V	
		$I_{O} = 6 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.25	0.40	-	0.50	V	
		I_{O} = 12 mA; V_{CC} = 4.5 V	-	0.35	0.55	-	0.65	V	
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	1.0	-	1.0	μA	
сс	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	20.0	-	40	μA	
VI _{CC}	additional supply current	per input; V _I = V _{CC} – 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	-	850	μΑ	
4	input capacitance		-	3.5	-	-	-	pF	

[1] Typical values are measured at T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions		-40	°C to +85	5 °C	–40 °C to +125 °C		Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	[2]						
		V _{CC} = 1.2 V		-	70	-	-	-	ns
		$V_{CC} = 2.0 V$		-	24	32	-	41	ns
		$V_{CC} = 2.7 V$		-	18	24	-	30	ns
		V_{CC} = 3.0 V to 3.6 V; C_L = 15 pF	[3]	-	11	-	-	-	ns
		V_{CC} = 3.0 V to 3.6 V	[3]	-	13	19	-	24	ns
		V_{CC} = 4.5 V to 5.5 V		-	-	16	-	20	ns
C _{PD}	power dissipation capacitance	C_L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC}	<u>[4]</u>	-	30	-	-	-	pF

[1] All typical values are measured at $T_{amb} = 25$ °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $\mathsf{P}_{\mathsf{D}} = \mathsf{C}_{\mathsf{P}\mathsf{D}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_i \times \mathsf{N} + \Sigma(\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_o) \text{ where:}$

 $f_i = \text{input}$ frequency in MHz, $f_o = \text{output}$ frequency in MHz

 C_{L} = output load capacitance in pF

 V_{CC} = supply voltage in V

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

11. Waveforms

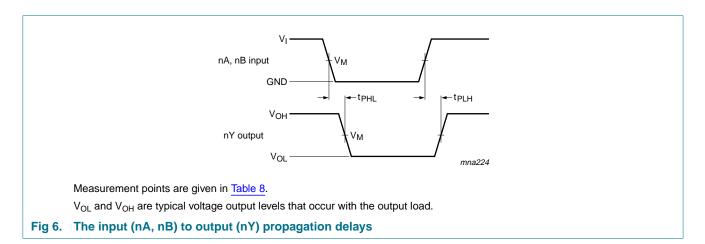


Table 8.Measurement points

Supply voltage	Input	Output
V _{CC}	V _M	V _M
< 2.7 V	0.5V _{CC}	0.5V _{CC}
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	0.5V _{CC}	0.5V _{CC}

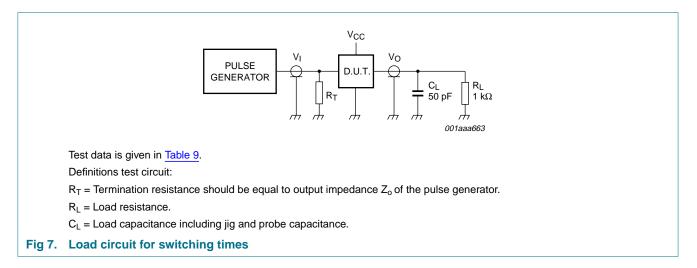


Table 9. Test data

Supply voltage	Input	Input			
V _{cc}	VI	t _r , t _f			
< 2.7 V	V _{CC}	≤ 2.5 ns			
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns			
≥ 4.5 V	V _{CC}	≤ 2.5 ns			

74LV86_3

Quad 2-input exclusive-OR gate

12. Package outline

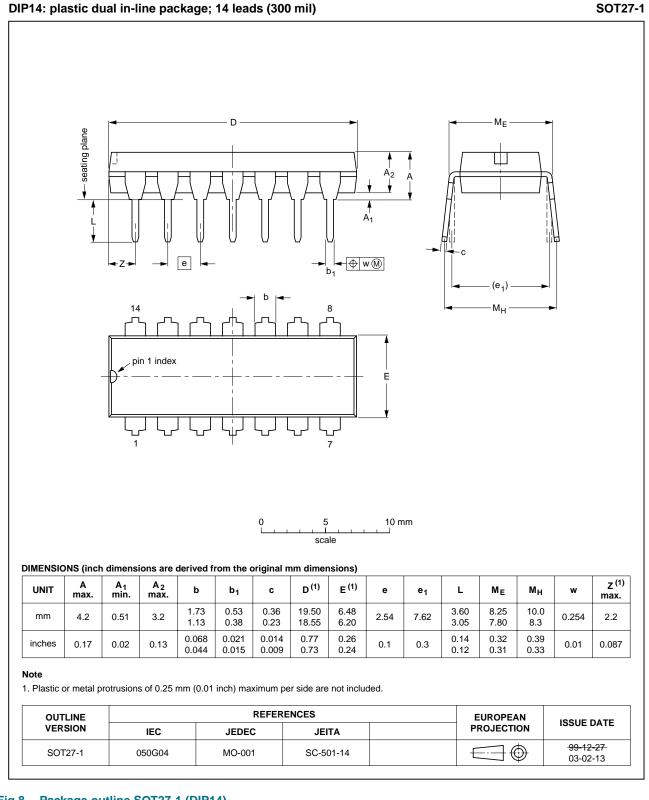


Fig 8. Package outline SOT27-1 (DIP14)

74LV86_3

Product data sheet

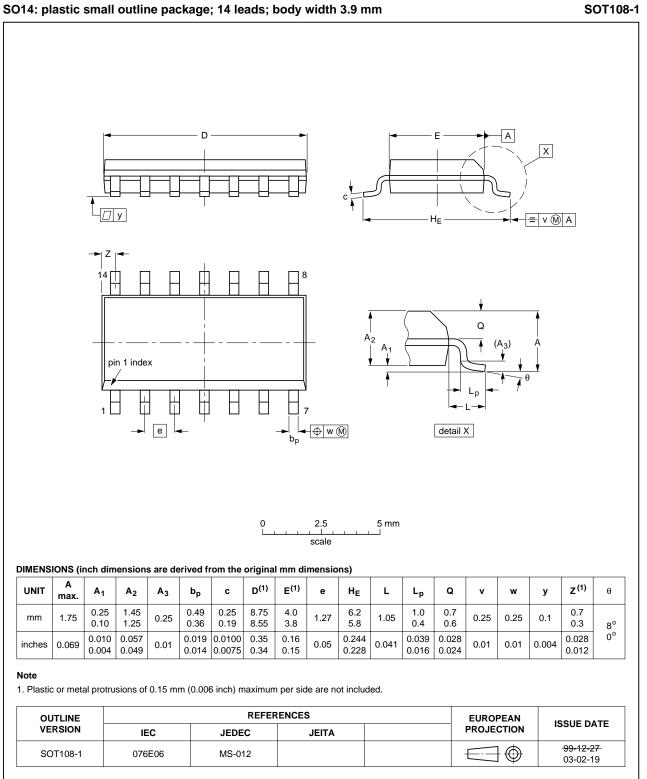


Fig 9. Package outline SOT108-1 (SO14)

74LV86_3

Product data sheet

Quad 2-input exclusive-OR gate

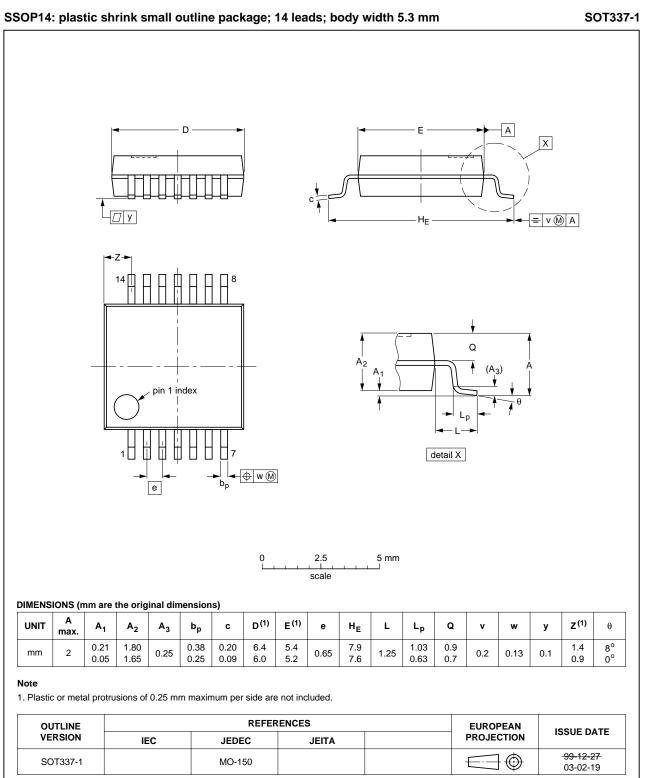


Fig 10. Package outline SOT337-1 (SSOP14)

74LV86_3

Product data sheet

Quad 2-input exclusive-OR gate

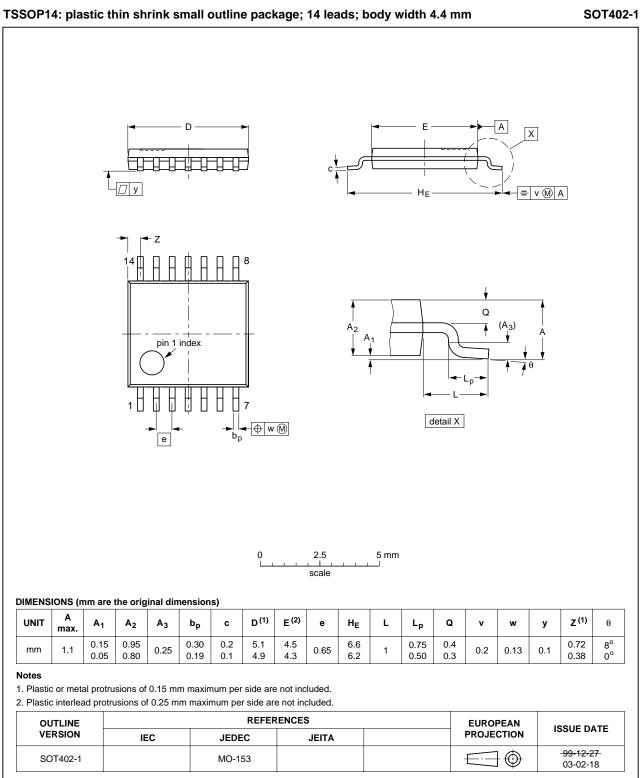
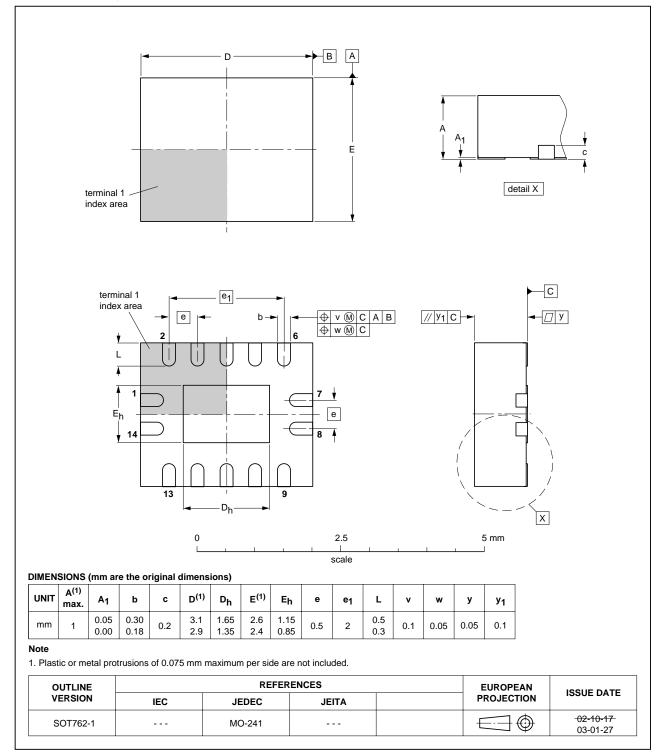


Fig 11. Package outline SOT402-1 (TSSOP14)

74LV86_3



DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

Fig 12. Package outline SOT762-1 (DHVQFN14)

74LV86_3

Product data sheet

13. Abbreviations

Table 10.	Abbreviations
Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74LV86_3	20071127	Product data sheet	-	74LV86_2		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidel of NXP Semiconductors. 					
	 Legal texts ha 	ve been adapted to the new	company name where	e appropriate.		
	 <u>Section 3</u>: DH 	VQFN14 package added.				
	 <u>Section 8</u>: der 	ating values added for DHV	QFN14 package.			
	 <u>Section 12</u>: οι 	utline drawing added for DH	/QFN14 package.			
74LV86_2	19980420	Product specification	-	74LV86_1		
74LV86_1	19970203	Product specification	-	-		

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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